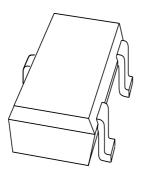
DISCRETE SEMICONDUCTORS

DATA SHEET



PMSTA92 PNP high-voltage transistor

Product data sheet Supersedes data of 1999 Jun 01 2001 Feb 20



PNP high-voltage transistor

PMSTA92

FEATURES

- S-mini package
- High voltage.

APPLICATIONS

• Primarily intended for use in telephony and professional communication equipment.

DESCRIPTION

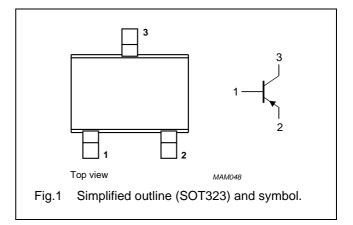
PNP transistor in a microminiature (SMD) plastic package intended for surface mounted applications.

MARKING

TYPE NUMBER	MARKING CODE
PMSTA92	tD2

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-300	V
V _{CEO}	collector-emitter voltage	open base	_	-300	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	625	K/W	

Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

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CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$V_{CB} = -200 \text{ V}; I_E = 0$	_	_	-100	nA
I _{EBO}	emitter cut-off current	$V_{BE} = -3 \text{ V}; I_{C} = 0$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V}$	40	_	_	
		$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}$	40	_	_	
		$I_C = -30 \text{ mA}; V_{CE} = -10 \text{ V}$	30	_	_	
V _{CEsat}	saturation voltage	$I_C = -20 \text{ mA}$; $I_B = -2 \text{ mA}$; note 1	_	_	-250	mV
V _{BEsat}	saturation voltage	$I_C = -20 \text{ mA}$; $I_B = -2 \text{ mA}$; note 1	_	_	-900	mV
C _c	collector-base capacitance	$V_{CB} = -20 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	1.9	3.5	pF
C _e	emitter-base capacitance	$V_{EB} = -5 \text{ V}; I_C = i_C = 0; f = 1 \text{ MHz}$	_	20	_	pF
f _T	transition frequency	$V_{CE} = -20 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	50	_	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

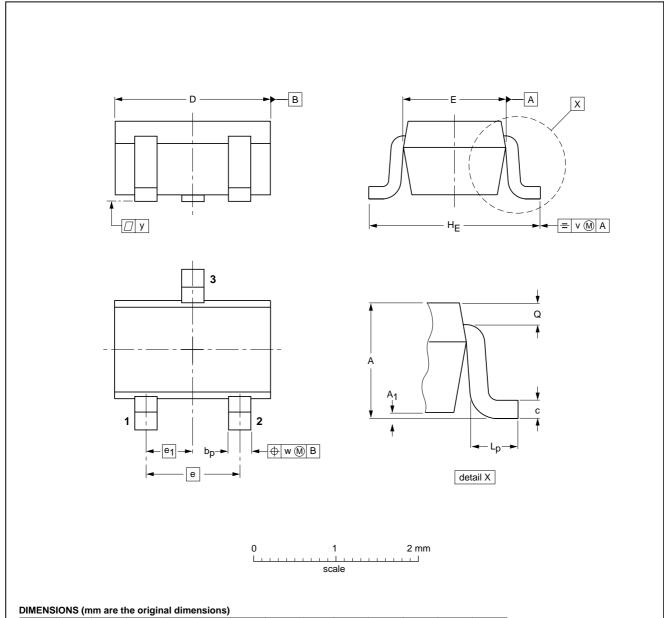
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



UNIT	Α	A ₁ max	bp	ပ	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	EUROPEAN ISSUE DATE				
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT323			SC-70			97-02-28	

PNP high-voltage transistor

PMSTA92

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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